

## SOT-23 Plastic-Encapsulate MOSFETS

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
20V	55 mΩ@ 4.5V	4A
	85 mΩ@ 2.5V	

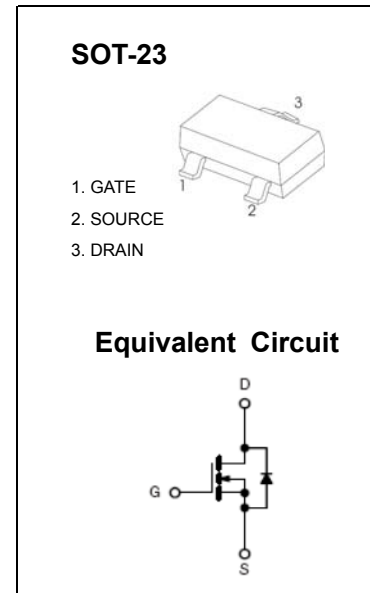
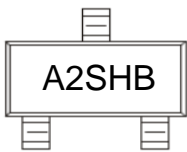
### FEATURE

- TrenchFET Power MOSFET

### APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

### MARKING



### Maximum ratings ( $T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	±12	
Continuous Drain Current	$I_D$	4	A
Pulsed Drain Current	$I_{DM}$	10	
Continuous Source-Drain Current(Diode Conduction)	$I_S$	1	
Maximum Power Dissipation	$P_D$	1.25	W
Thermal Resistance from Junction to Ambient( $t \leq 5s$ )	$R_{\theta JA}$	100	$^{\circ}C/W$
Junction Temperature	$T_J$	150	$^{\circ}C$
Storage Temperature	$T_{stg}$	-55~+150	

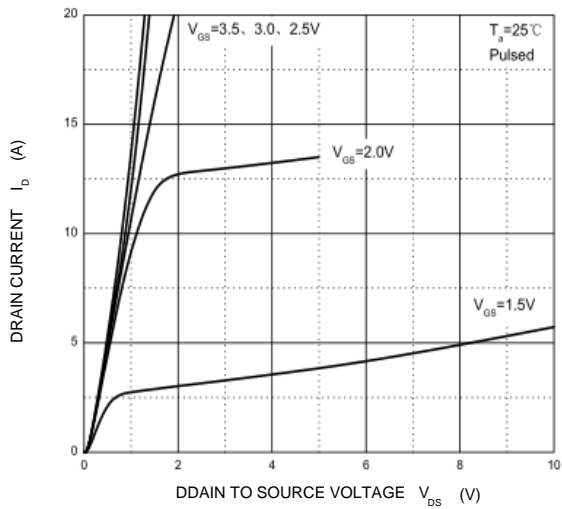
**MOSFET ELECTRICAL CHARACTERISTICS**
**T<sub>a</sub>=25 °C unless otherwise specified**

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Static</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	20	21.5		V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	0.4	0.7	1	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±12V			±100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V			1	μA
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.0A		45	55	mΩ
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 2.0A		63	85	
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 3.6A		8		S
<b>Dynamic <sup>b</sup></b>						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1MHz		300		pF
Output capacitance	C <sub>oss</sub>			120		
Reverse transfer capacitance	C <sub>rss</sub>			80		
<b>Switching characteristics(note4 )</b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>GS</sub> = 10V, V <sub>GEN</sub> = 4.5V R <sub>L</sub> = 5.5Ω, R <sub>g</sub> = 6Ω			15	ns
Rise time	t <sub>r</sub>				80	
Turn-off delay time	t <sub>d(off)</sub>				60	
Fall time	t <sub>f</sub>				25	
<b>Drain-source body diode characteristics</b>						
Body diode voltage (note3)	V <sub>SD</sub>	I <sub>S</sub> = 1A		0.8	1.0	V

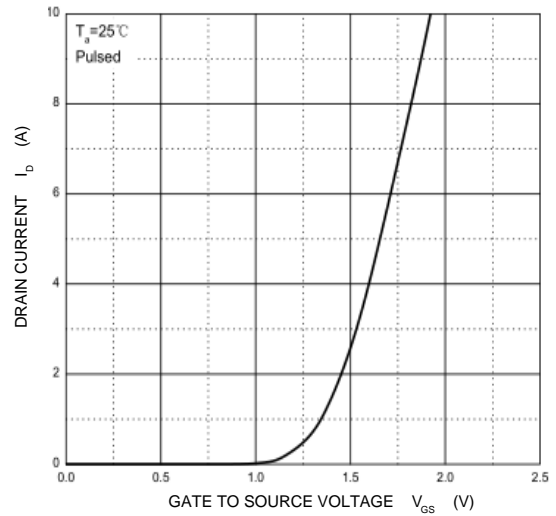
**Notes :**

- a. Pulse Test : Pulse width < 300us, duty cycle < 2%.
- b. These parameters have no way to verify.

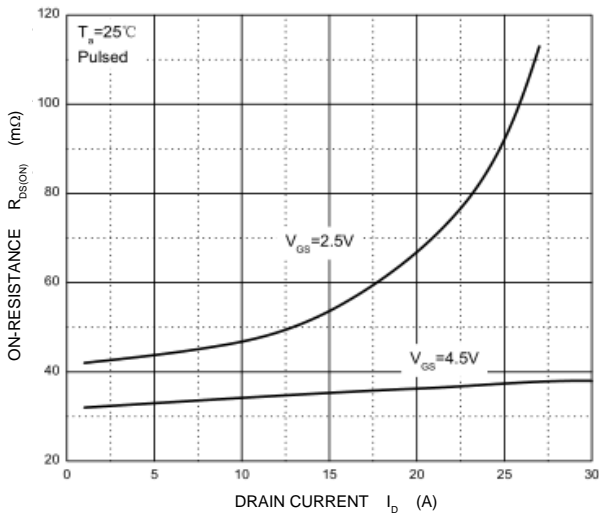
### Output Characteristics



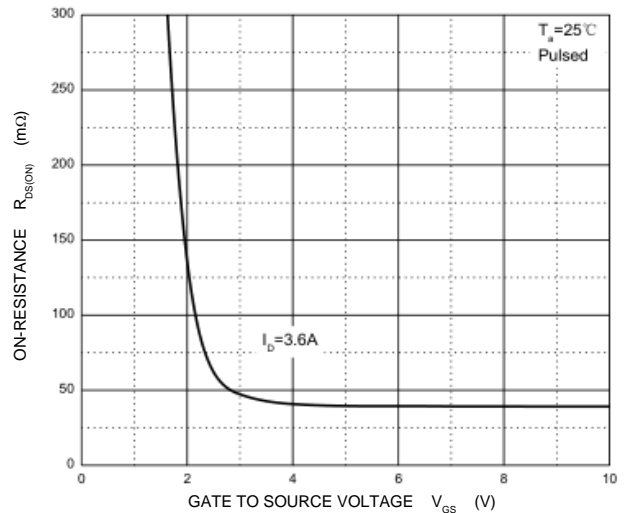
### Transfer Characteristics



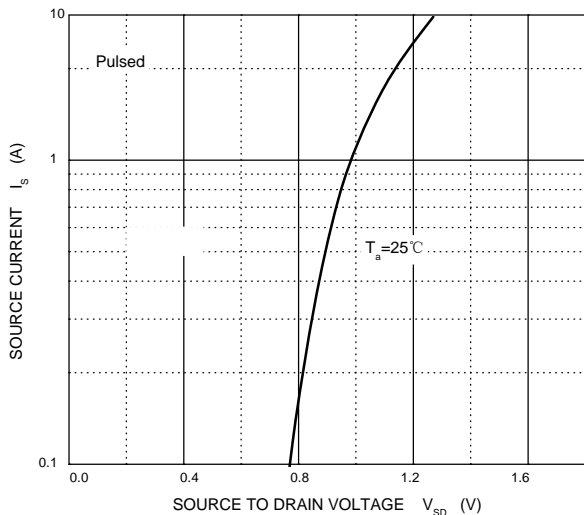
### $R_{DS(ON)}$ — $I_D$



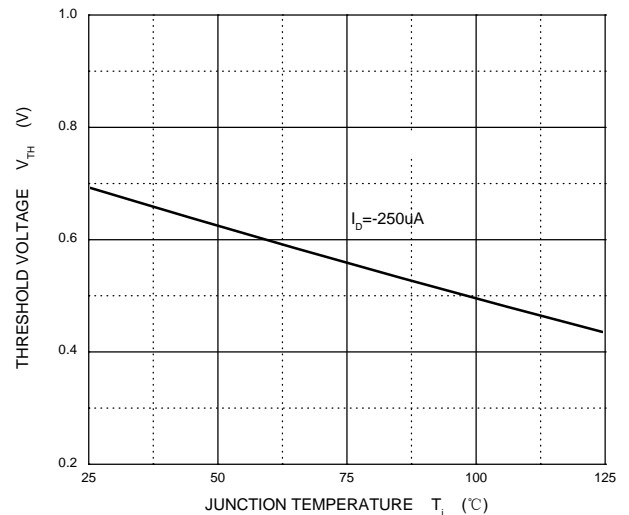
### $R_{DS(ON)}$ — $V_{GS}$

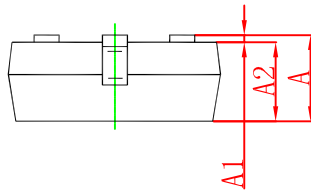
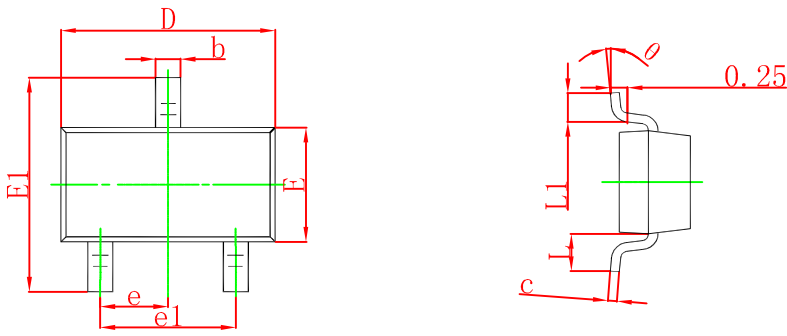


### $I_S$ — $V_{SD}$



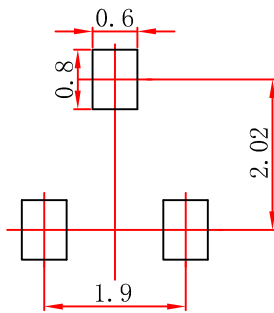
### Threshold Voltage





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

### SOT-23 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance:  $\pm 0.05\text{mm}$ .
  3. The pad layout is for reference purposes only.